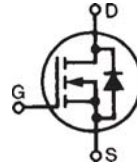


# HiPerFET™

## Power MOSFETs

### Q2-Class

## IXFH14N100Q2



N-Channel Enhancement Mode  
 Avalanche Rated, High dv/dt, Low  $Q_g$   
 Low intrinsic  $R_g$ , low  $t_{rr}$

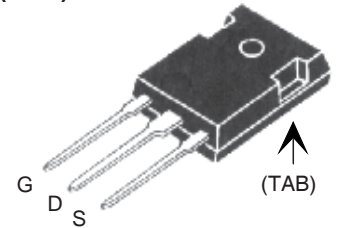
$$V_{DSS} = 1000V$$

$$I_{D25} = 14A$$

$$R_{DS(on)} \leq 950m\Omega$$

$$t_{rr} \leq 300ns$$

TO-247 (IXFH)



G = Gate  
 S = Source

D = Drain  
 TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	1000	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	1000	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	14	A
$I_{DM}$	$T_C = 25^\circ C$ , pulse width limited by $T_{JM}$	56	A
$I_A$	$T_C = 25^\circ C$	14	A
$E_{AS}$	$T_C = 25^\circ C$	2.5	J
dV/dt	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	20	V/ns
$P_D$	$T_C = 25^\circ C$	500	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6mm (0.063 in) from case for 10s	300	$^\circ C$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
<b>Weight</b>		6	g

### Features

- Double metal process for low gate resistance
- International standard package
- Epoxy meet UL94 V-0, flammability classification
- Avalanche energy and current rated
- Fast intrinsic Rectifier

### Applications

- DC-DC converters
- Switched-mode and resonant-mode power supplies, >500kHz switching
- DC choppers
- Pulse generation
- Laser drivers

### Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$V_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu A$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4mA$	3.0		5.5 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$			25 $\mu A$ 1 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			950 m $\Omega$

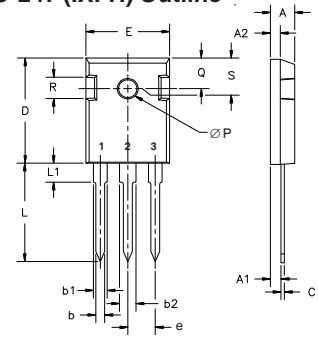
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}, I_D = 0.5 \cdot I_{D25}$ , Note 1	15	28	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		2800	pF
$C_{oss}$			287	pF
$C_{rss}$			100	pF
$t_{d(on)}$	Resistive Switching Times		12	ns
$t_r$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		10	ns
$t_{d(off)}$	$R_G = 2\Omega$ (External)		28	ns
$t_f$			12	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		83	nC
$Q_{gs}$			20	nC
$Q_{gd}$			40	nC
$R_{thJC}$			0.25	$^\circ\text{C/W}$
$R_{thCK}$		0.21		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			14 A
$I_{SM}$	Repetitive, pulse width limited by $T_{JM}$			56 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 25\text{A}, -di/dt = 100\text{A}/\mu\text{s}, V_R = 100\text{V}$		0.8	300 ns
$Q_{RM}$			7	$\mu\text{C}$
$I_{RM}$				A

Notes: 1. Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

### TO-247 (IXFH) Outline



Terminals: 1 - Gate 2 - Drain

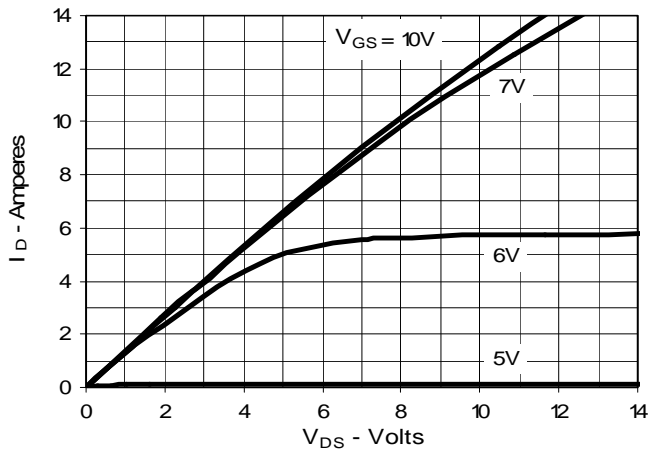
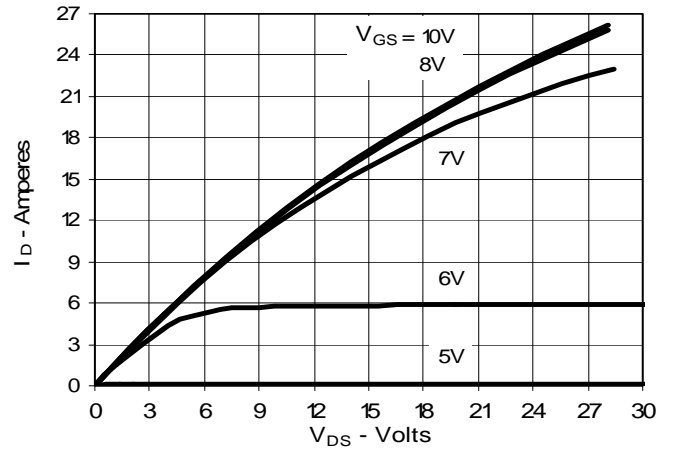
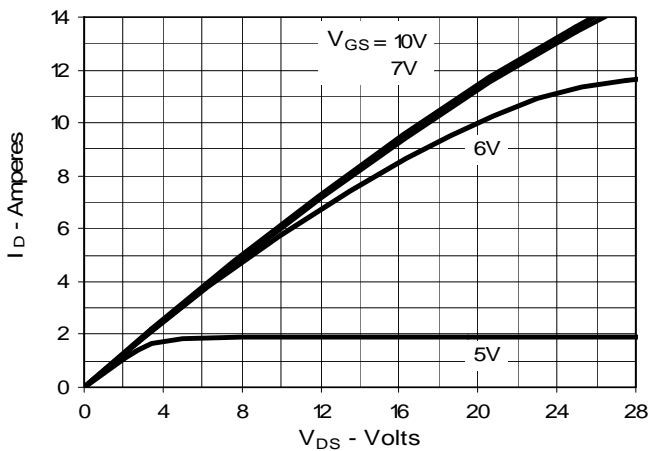
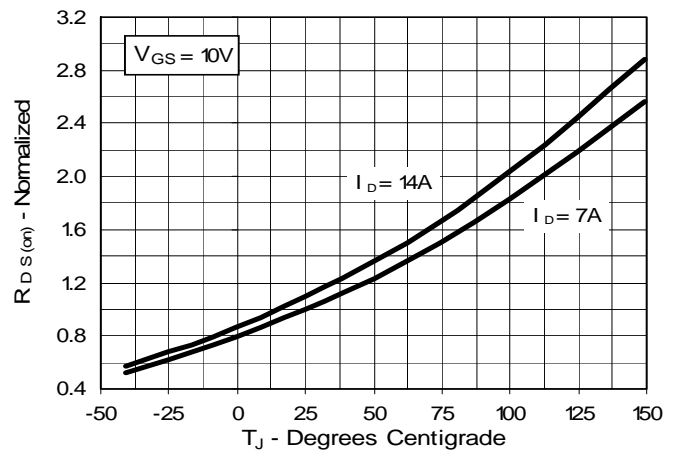
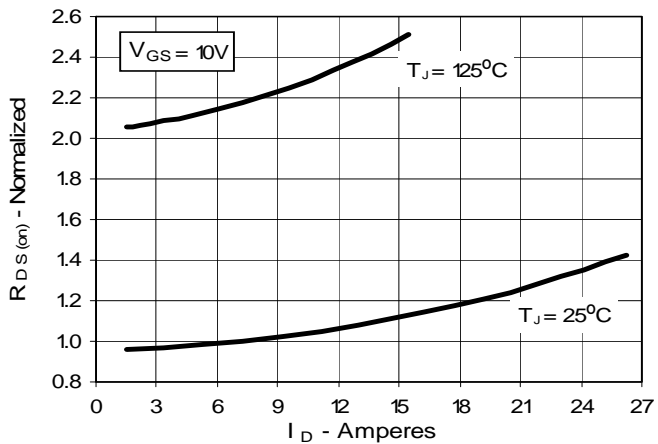
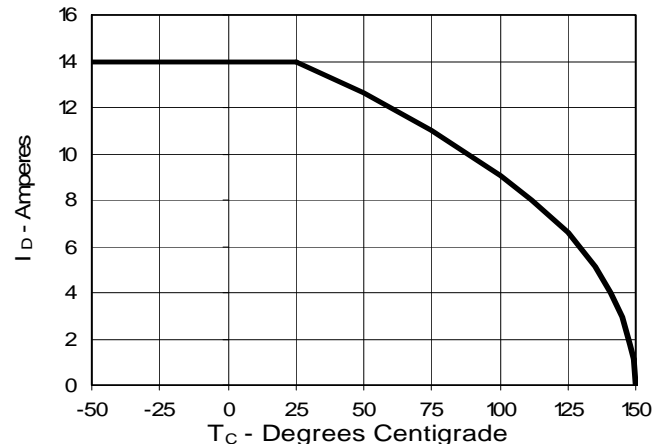
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216

### PRELIMINARY TECHNICAL INFORMATION

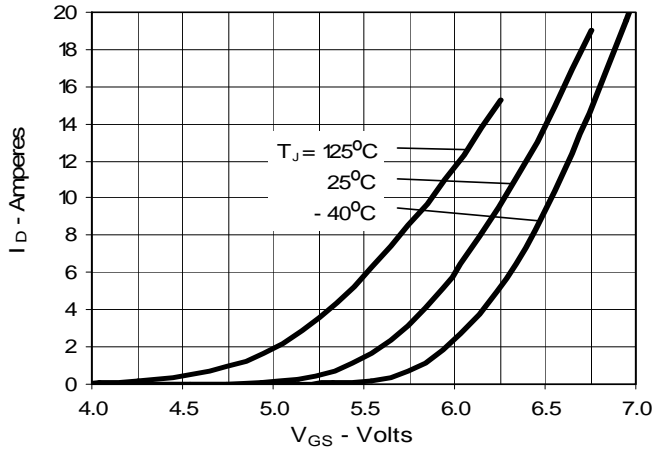
The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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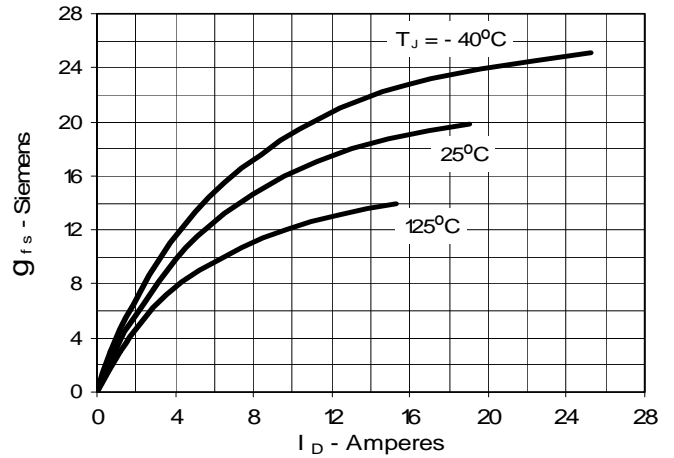
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics**  
 @ 25°C

**Fig. 2. Extended Output Characteristics**  
 @ 25°C

**Fig. 3. Output Characteristics**  
 @ 125°C

**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs.  $I_D$** 

**Fig. 6. Drain Current vs. Case Temperature**


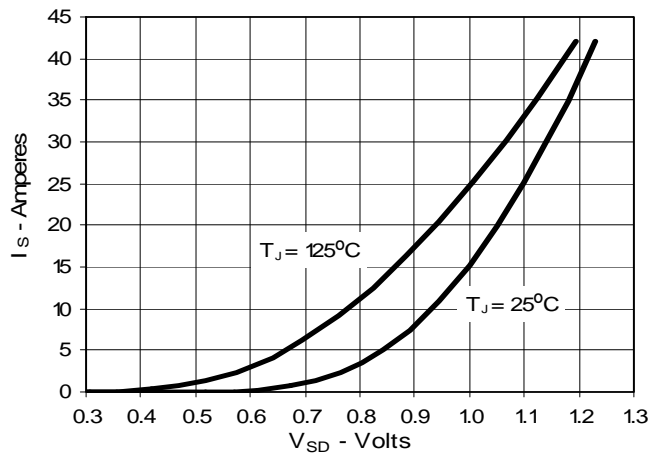
**Fig. 7. Input Admittance**



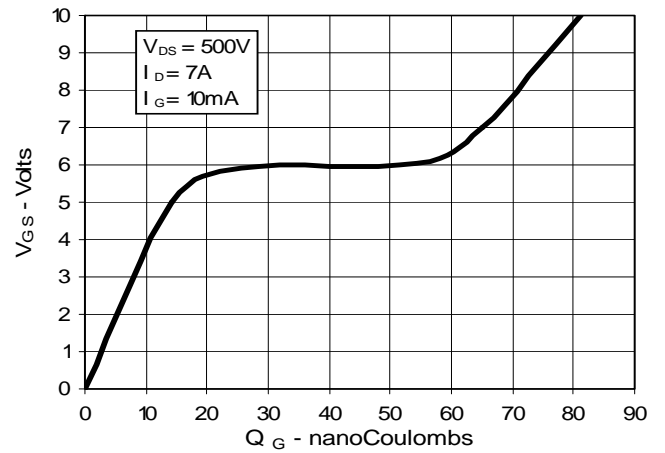
**Fig. 8. Transconductance**



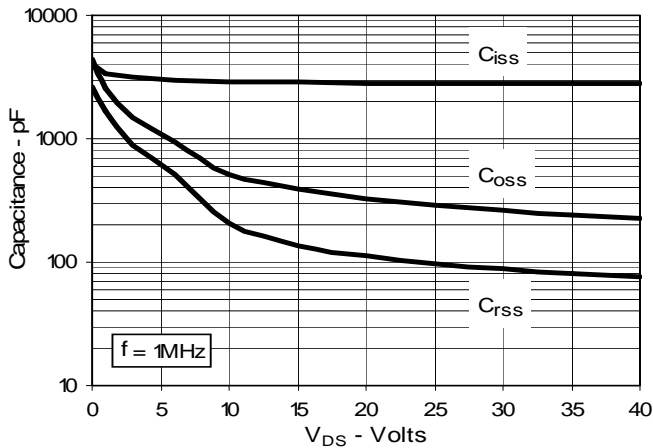
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Impedance**

